2SK1307

Silicon N-Channel MOS FET

HITACHI

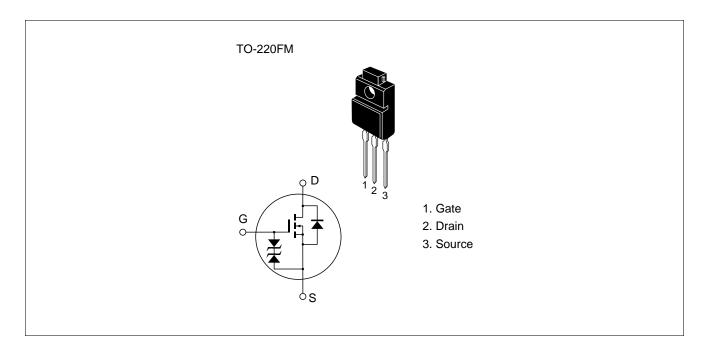
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- 4 V gate drive device
 - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

Outline





2SK1307

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{\scriptscriptstyle DSS}$	100	V
Gate to source voltage	$V_{\sf GSS}$	±20	V
Drain current	I _D	20	А
Drain peak current	I _{D(pulse)} *1	80	Α
Body to drain diode reverse drain current	I _{DR}	20	А
Channel dissipation	Pch*2	35	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

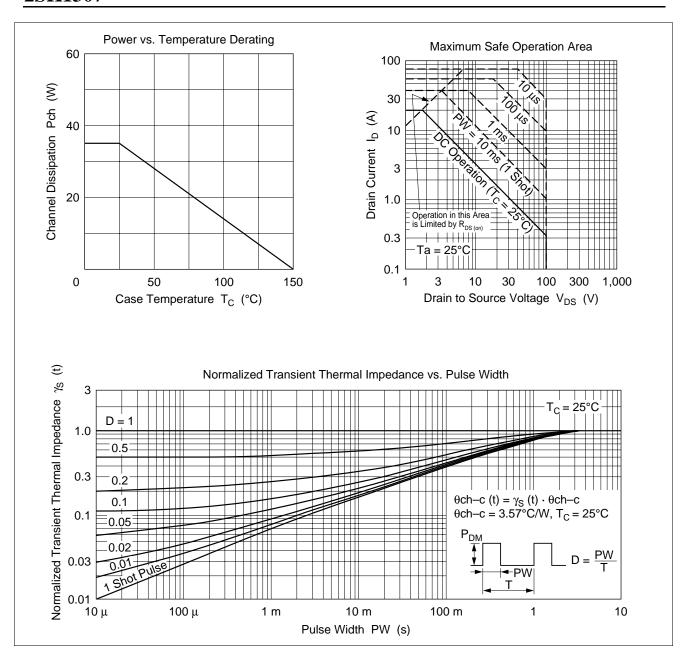
2. Value at $T_c = 25^{\circ}C$

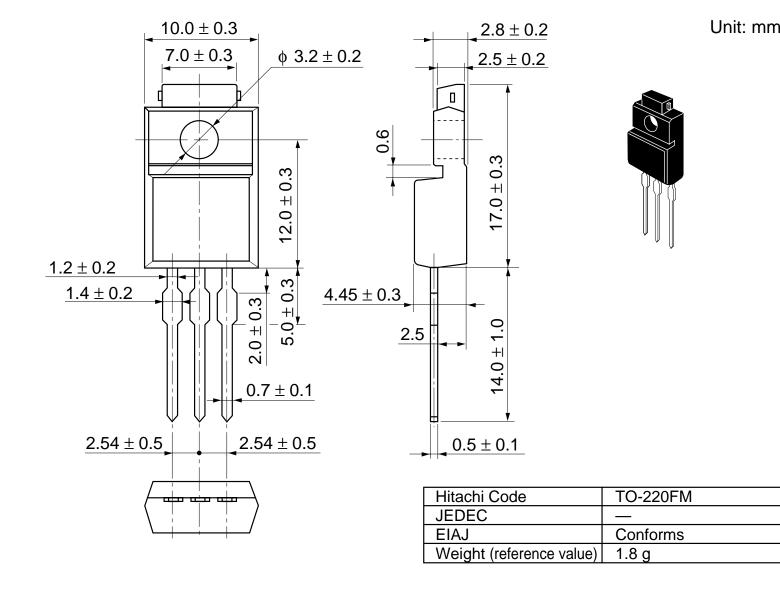
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	250	μΑ	$V_{DS} = 80 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{\rm GS(off)}$	1.0	_	2.0	V	$I_{D} = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	R _{DS(on)}	_	0.065	0.085	Ω	$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
		_	0.085	0.12	Ω	$I_D = 10 \text{ A}, V_{GS} = 4 \text{ V}^{*1}$
Forward transfer admittance	yfs	10	16	_	S	$I_D = 10 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	Ciss	_	1300	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	540	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	160	_	pF	
Turn-on delay time	t _{d(on)}	_	12	_	ns	$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time	t _r	_	100	_	ns	$R_L = 3 \Omega$
Turn-off delay time	t _{d(off)}	_	300	_	ns	
Fall time	t _f	_	150	_	ns	
Body to drain diode forward voltage	V_{DF}	_	1.3	_	V	$I_F = 20 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t _{rr}		300		ns	$I_F = 20 \text{ A}, V_{GS} = 0,$ $di_F/dt = 50 \text{ A}/\mu\text{s}$

Note: 1. Pulse test

See characteristic curves of 2SK1302.





Cautions

- 1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
- 2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
- 3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
- 4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as failsafes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
- 5. This product is not designed to be radiation resistant.
- 6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
- 7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica http:semiconductor.hitachi.com/ Europe

http://www.hitachi-eu.com/hel/ecg http://www.has.hitachi.com.sg/grp3/sicd/index.htm http://www.hitachi.com.tw/E/Product/SICD_Frame.htm Asia (Singapore) Asia (Taiwan) Asia (HongKong) http://www.hitachi.com.hk/eng/bo/grp3/index.htm

http://www.hitachi.co.jp/Sicd/indx.htm Japan

For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose,CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Hitachi Europe GmbH Electronic components Group Dornacher Stra§e 3 D-85622 Feldkirchen, Munich Germany

Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd. Flectronic Components Group Whitebrook Park Lower Cookham Road Maidenhead

Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd. Taipei Branch Office

3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281

Telex: 40815 HITEC HX

Copyright ' Hitachi, Ltd., 1999. All rights reserved. Printed in Japan.